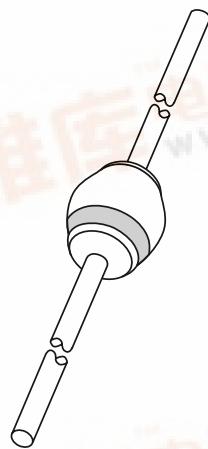


## DISCRETE SEMICONDUCTORS

# DATA SHEET



## BY278 Damper diode

Product specification

1996 Sep 26

## Damper diode

BY278

## FEATURES

- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Available in ammo-pack
- Also available with preformed leads for easy insertion.

## DESCRIPTION

Rugged glass package, using a high temperature alloyed construction.

This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

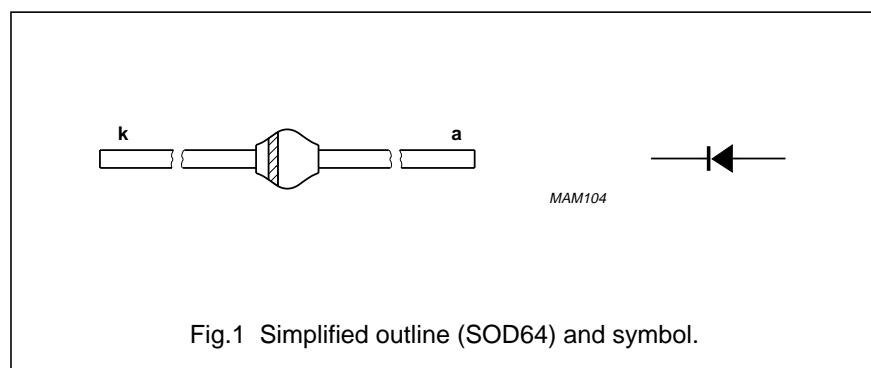


Fig.1 Simplified outline (SOD64) and symbol.

## APPLICATIONS

- Damper diode in high frequency horizontal deflection circuits up to 16 kHz.

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{RSM}$	non-repetitive peak reverse voltage		–	1700	V
$V_{RRM}$	repetitive peak reverse voltage		–	1700	V
$V_R$	continuous reverse voltage		–	1650	V
$I_{FWM}$	working peak forward current	$T_{amb} = 75^\circ\text{C}$ ; PCB mounting (see Fig.4); see Fig.2	–	5	A
$I_{FRM}$	repetitive peak forward current		–	10	A
$I_{FSM}$	non-repetitive peak forward current	$t = 10\text{ ms}$ half sinewave; $T_j = T_{j\max}$ prior to surge; $V_R = V_{RRM\max}$	–	50	A
$T_{stg}$	storage temperature		–65	+175	$^\circ\text{C}$
$T_j$	junction temperature		–65	+150	$^\circ\text{C}$

## ELECTRICAL CHARACTERISTICS

$T_j = 25^\circ\text{C}$ ; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$V_F$	forward voltage	$I_F = 5\text{ A}$ ; $T_j = T_{j\max}$ ; see Fig.3	1.4	V
		$I_F = 5\text{ A}$ ; see Fig.3	1.5	V
$I_R$	reverse current	$V_R = V_{R\max}$ ; $T_j = 150^\circ\text{C}$	150	$\mu\text{A}$
$t_{rr}$	reverse recovery time	when switched from $I_F = 0.5\text{ A}$ to $I_R = 1\text{ A}$ ; measured at $I_R = 0.25\text{ A}$ ; see Fig.6	1	$\mu\text{s}$
$t_{fr}$	forward recovery time	when switched to $I_F = 5\text{ A}$ in 50 ns; $T_j = T_{j\max}$ ; Fig.7	1	$\mu\text{s}$

## Damper diode

BY278

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\ -tp}$	thermal resistance from junction to tie-point	lead length = 10 mm	25	K/W
$R_{th\ j\ -a}$	thermal resistance from junction to ambient	note 1	75	K/W
		mounted as shown in Fig.5	40	K/W

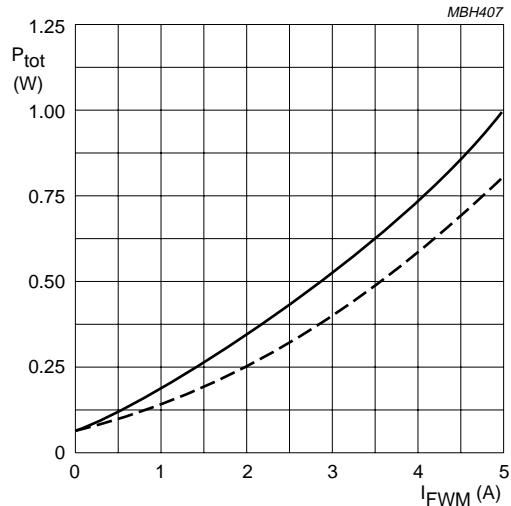
## Note

1. Device mounted on an epoxy-glass printed-circuit board, 1.5 mm thick; thickness of Cu-layer  $\geq$  40  $\mu\text{m}$ , see Fig.4. For more information please refer to the "General Part of associated Handbook".

## Damper diode

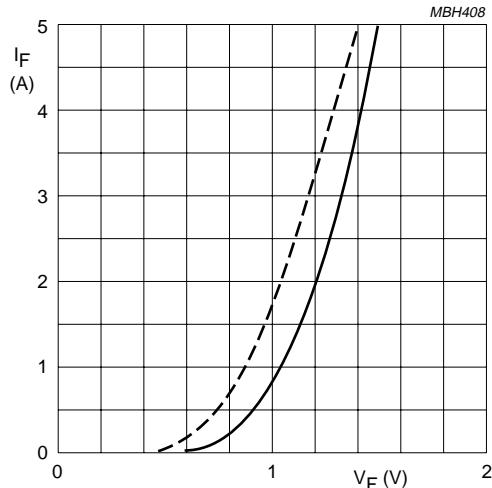
BY278

## GRAPHICAL DATA



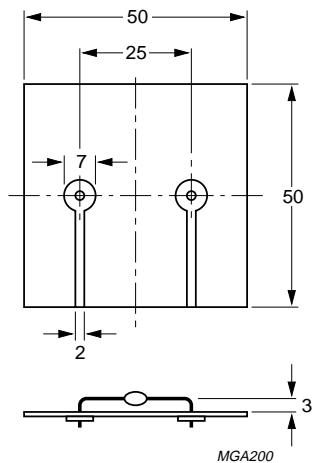
Solid line: basic high-voltage E/W modulator circuit; see Fig.8.  
 Dotted line: basic conventional horizontal deflection circuit; see Fig.9.  
 Curves include power dissipation due to switching losses.

Fig.2 Maximum total power dissipation as a function of working peak forward current.



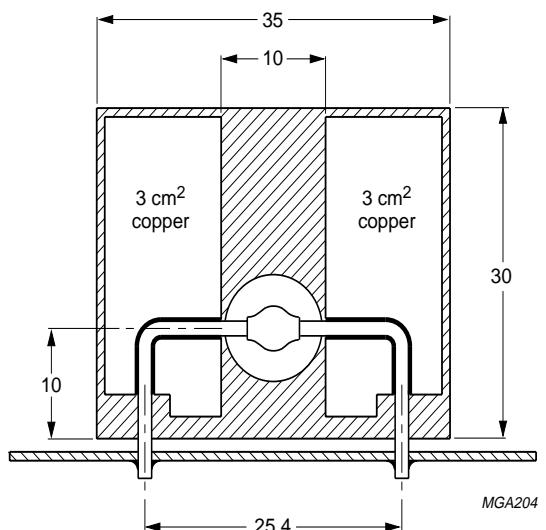
Dotted line:  $T_j = 150 \text{ }^\circ\text{C}$ .  
 Solid line:  $T_j = 25 \text{ }^\circ\text{C}$ .

Fig.3 Forward current as a function of forward voltage; maximum values.



Dimensions in mm.

Fig.4 Device mounted on a printed-circuit board.

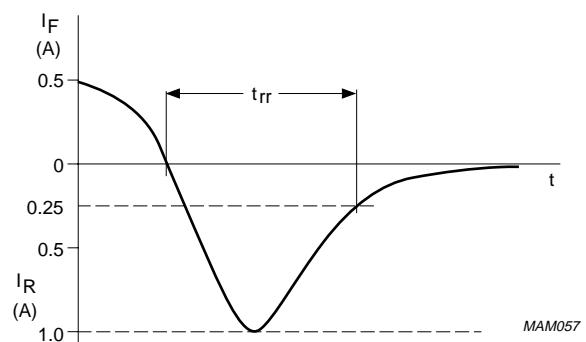
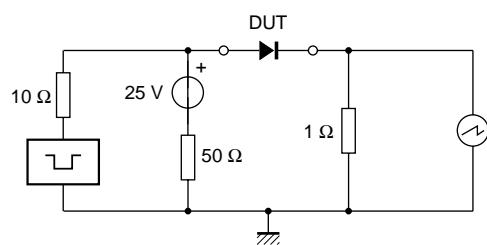


Dimensions in mm.

Fig.5 Mounting with additional printed-circuit board for heat sink purposes.

## Damper diode

BY278



Input impedance oscilloscope:  $1 \text{ M}\Omega$ ,  $22 \text{ pF}$ ;  $t_r \leq 7 \text{ ns}$ .  
 Source impedance:  $50 \Omega$ ;  $t_r \leq 15 \text{ ns}$ .

Fig.6 Test circuit and reverse recovery time waveform and definition.

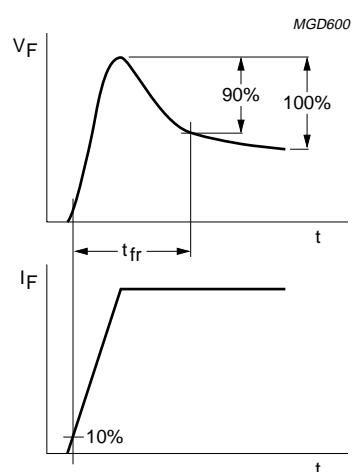


Fig.7 Forward recovery time definition.

## Damper diode

BY278

## APPLICATION INFORMATION

For horizontal deflection circuits, two basic applications are shown in Figs 8 and 9.

The maximum allowable total power dissipation for the diode can be calculated from the thermal resistance  $R_{th\ j-a}$  and the difference between  $T_{j\ max}$  and  $T_{amb\ max}$  in the application. The maximum  $I_{FWM}$  can then be taken from Fig.2.

The basic application waveforms in Fig.10 relate to the circuit in Fig.8. In the circuit in Fig.9 the forward conduction time of the diode is shorter, allowing a higher  $I_{FWM}$  (see Fig.2).

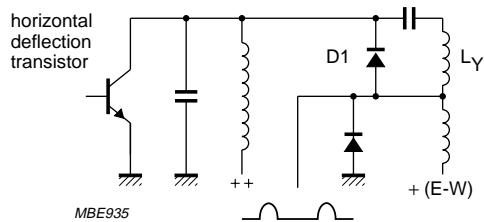


Fig.8 Application in basic high-voltage E/W modulator circuit.

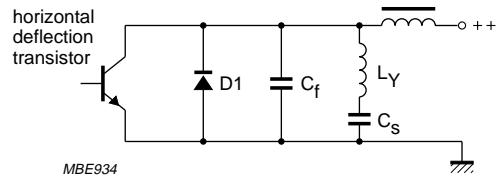


Fig.9 Application in basic horizontal deflection circuit.

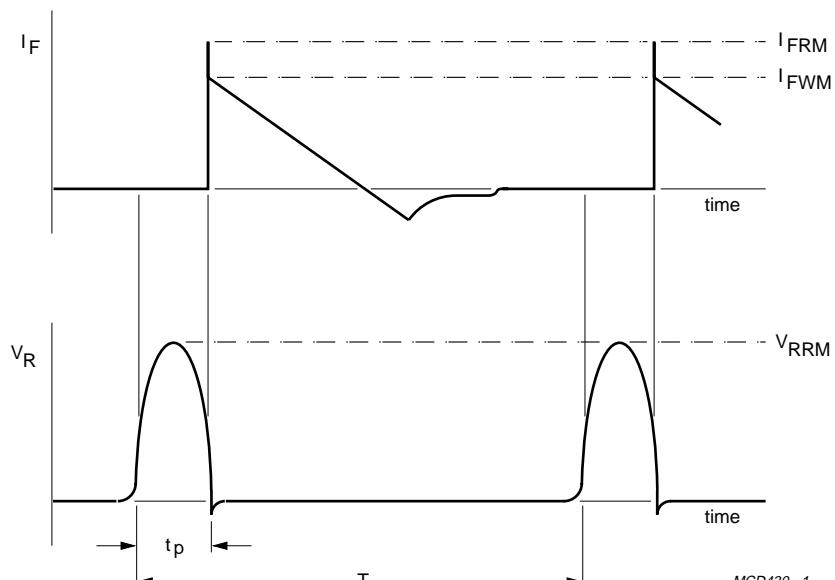
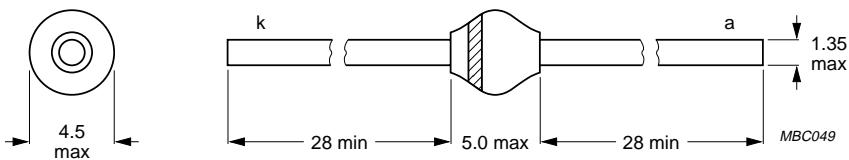


Fig.10 Basic application waveforms.

## Damper diode

BY278

## PACKAGE OUTLINE



Dimensions in mm.

The marking band indicates the cathode.

Fig.11 SOD64.

## DEFINITIONS

## Data Sheet Status

Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.

## Limiting values

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

## Application information

Where application information is given, it is advisory and does not form part of the specification.

## LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.